

FEATURES:

GaAsP/GaP Amber Chip

Amber Diffused Lens

Low Power Requirements

Wide Viewing Angle

ABSOLUTE MAXIMUM RATINGS

(Ta=25°C)

Power dissipation/Chip	Pd	60mW
Continuous Forward Current/Chip	IF	20mA
Peak Forward Current/Chip (*Pulse Width = 1ms , Duty Ratio = 1/10)	*IFP	100mA
Reverse Voltage	VR	5V
Operating Temperature Range	Topr	-20 to +80°C
Storage Temperature Range	Tstg	-25 to +85°C
Solder Temperature (1/16 Inch from body)		260°C
Maximum Soldering Time(≤260°C)		5 sec

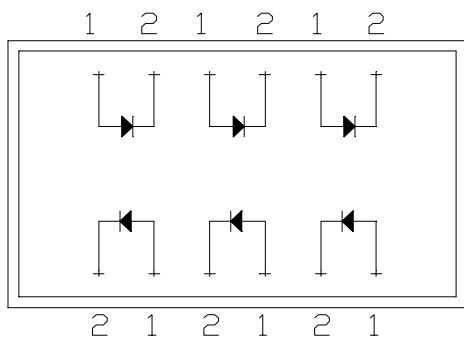
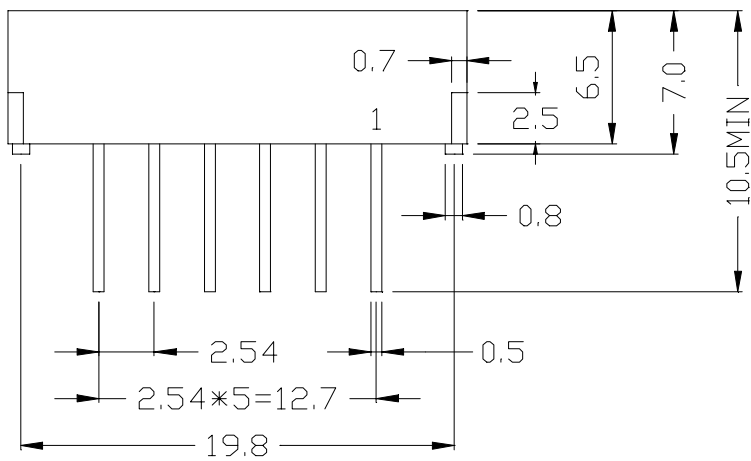
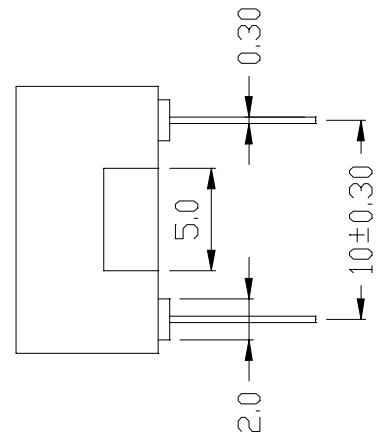
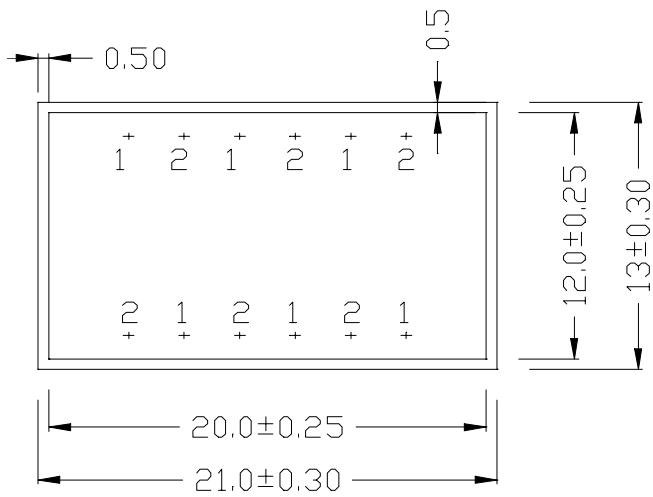
ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage/Chip	V _F		2.1	2.8	V	I _F =20mA
Reverse Current/Chip	I _R			100	μA	V _R =5V
Peak Wavelength	λ _p		589		nm	I _F =20mA
Dominant Wavelength	λ _d		590		nm	I _F =20mA
Spectral Line Half Width	Δλ		35		nm	I _F =20mA
Luminous Intensity	IV	5	15		mcd	I _F =10mA/Chip



M2012Y



Pin connection :

1: Anode
2: Cathode

Unit : mm

Tol. : ± 0.3 mm unless otherwise noted